DSK Diode Semiconductor Korea *BY550-50 --- BY550-1000*

PLASTIC SILICON RECTIFIERS

VOLTAGE RANGE: 50 --- 1000 V
CURRENT: 5.0 A

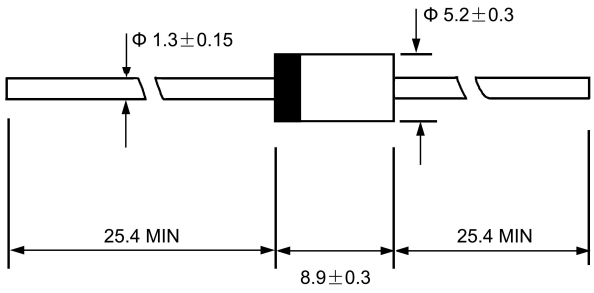
FEATURES

- ◇ Low cost
- ◇ Diffused junction
- ◇ Low leakage
- ◇ Low forward voltage drop
- ◇ High current capability
- ◇ Easily cleaned witn Freon,Alcohol,Isopropanol and similar solvents
- ◇ The plastic material carries U/L recognition 94V-0

MECHANICAL DATA

- ◇ Case:JEDEC DO-27,molded plastic
- ◇ Terminals: Axial lead ,solderable per MIL- STD-202,Method 208
- ◇ Polarity: Color band denotes cathode
- ◇ Weight: 0.041 ounces, 1.15 grams
- ◇ Mounting position: Any

DO - 27



Dimensions in millimeters

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25℃ ambient temperature unless otherwise specified.

Single phase,half wave,60 Hz,resistive or inductive load. For capacitive load,derate by 20%.

		BY 550-50	BY 550-100	BY 550-200	BY 550-400	BY 550-600	BY 550-800	BY 550-1000	UNITS
Maximum recurrent peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum average forward rectified current 9.5mm lead length, @T_A=75℃	$I_{F(AV)}$	5.0							A
Peak forward surge current 8.3ms single half-sine-wave superimposed on rated load @T_J=125℃	I_{FSM}	300.0							A
Maximum instantaneous forward voltage @ 5.0 A	V_F	1.1							V
Maximum reverse current @T_A=25℃	I_R	10.0							μA
at rated DC blocking voltage @T_A=100℃		100.0							
Typical junction capacitance (Note1)	C_J	80							pF
Typical thermal resistance (Note2)	$R_{\theta JA}$	15							℃/W
Operating junction temperature range	T_J	- 55 ---- + 150							℃
Storage temperature range	T_{STG}	- 55 ---- + 150							℃

NOTE: 1. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

2. Thermal resistance from junction to ambient.

FIG.1 -- TYPICAL FORWARD CHARACTERISTICS

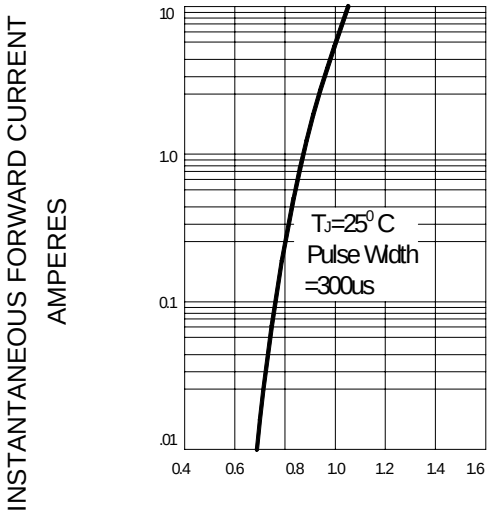


FIG.2 -- TYPICAL FORWARD DERATING CURVE

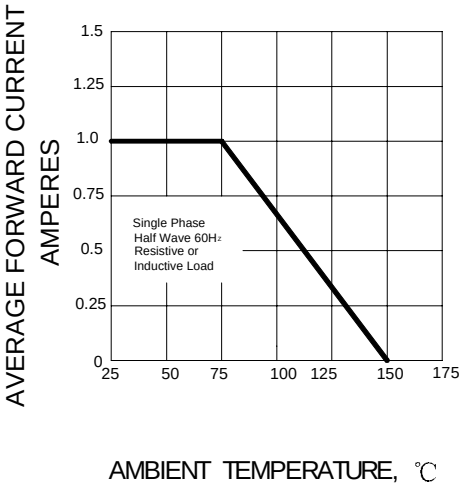


FIG.3 -- PEAK FORWARD SURGE CURRENT

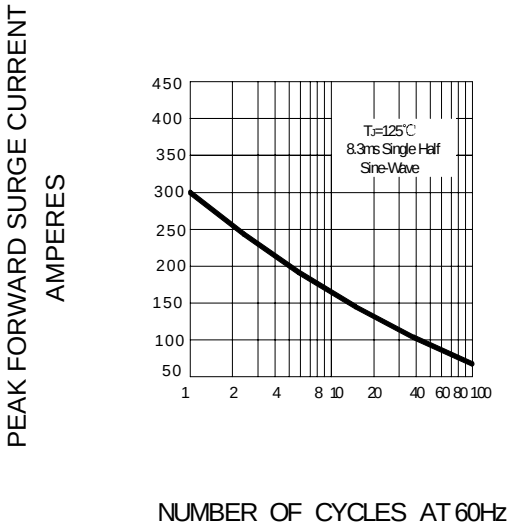


FIG.4--TYPICAL JUNCTION CAPACITANCE

